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RLT808100GS TECHNICAL DATA

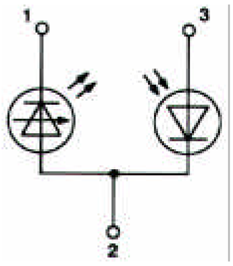
High Power Infrared Laserdiode

Structure: **AlGaAs/GaAs quantum well, aperture 3 x 1 µm**
Lasing wavelength: **808 +/- 3 nm typ., singlemode**
Max. optical power: **110 mW**
Package: **9 mm**

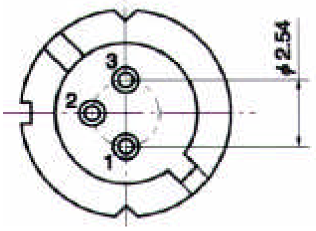
ATTENTION
OBSERVE PRECAUTIONS FOR HANDLING
ELECTROSTATIC SENSITIVE DEVICE

NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	110	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	5	V
Operating Temperature	T_C	-40 .. +60	°C
Storage Temperature	T_{STG}	-50 .. +80	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free		100		mW
Threshold Current	I_{th}		35	45	55	mA
Operation Current	I_{op}	P_o = 100 mW	140	200	220	mA
Lasing Wavelength	λ_p	P_o = 100 mW	805	808	810	nm
Beam Divergence	$\theta_{//}$	P_o = 100 mW		10		°
Beam Divergence	$\theta_{\perp}$	P_o = 100 mW		35		°
Differential Efficiency	dP_o/dI_{op}	P_o = 100 mW		0.75	1.0	mW/mA
Monitor Current	I_m	P_o = 100 mW	100	450	1000	µA